

23. (Twice amended) A chemical vapor deposition (CVD) process using ozone, for depositing films on a substrate assembly surface, said process comprising [the steps of]:
[(a)] disposing the substrate within a chemical vapor deposition reaction chamber;
[(b)] introducing a gas volume of a preselected reaction precursor compound into said chamber;
[(c)] admitting a gas volume of ozone into the chamber;
[(d)] exposing to a source of high intensity light the volume of gas located within [a chemically reactive distance of the substrate surface,] the reaction chamber without directly exposing the substrate assembly to the light source.
24. (Twice amended) A chemical vapor deposition (CVD) process for depositing films on a substrate surface, said process comprising [the steps of]:
[(a)] disposing the substrate within a chemical vapor deposition reaction chamber;
[(b)] introducing a gas volume of a first preselected reaction precursor compound into said chamber;
[(c)] admitting a gas volume of at least a second preselected reaction precursor compound into said chamber;
[(d)] optically exciting the volume of gas located within [a chemically reactive distance of the substrate,] the reaction chamber without directly exposing the substrate assembly surface to the optical excitation.
30. (Once amended) A method of [providing a chemical vapor deposition environment in] depositing a material on a substrate surface within a reaction chamber, the method comprising:
introducing a deposition gas into the chamber;
introducing ozone gas into the chamber; and
optically exciting gas located in a heterogeneous chemical reaction volume of the chamber without directing photons at the substrate surface.